

2STR2160

Low voltage fast-switching PNP power transistor

Datasheet - production data

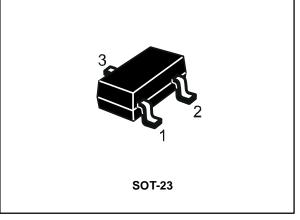
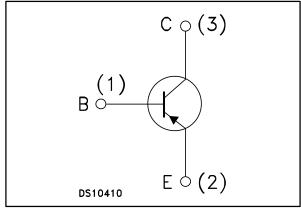


Figure 1: Internal schematic diagram



This is information on a product in full production.

Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package for surface mounting circuits

Applications

- LED
- Battery charger
- Motor and relay driver
- Voltage regulation

Description

The device in a PNP transistor manufactured using new "PB-HCD" (power bipolar high current density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

The complementary NPN is the 2STR1160.

Table 1: Device summary

Table 1. Device Summary				
Order code	Marking	Package	Packing	
2STR2160	2160	SOT-23	Tape and reel	

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1 Electrical ratings

 Table 2: Absolute maximum rating

Symbol	Parameter	Value	Unit
Vсво	Collector-base voltage ($I_E = 0$)	-60	V
V _{CEO}	Collector-emitter voltage $(I_B = 0)$	-60	V
VEBO	Emitter-base voltage (Ic = 0)	-5	V
lc	Collector current	-1	А
I _{CM}	Collector peak current (t _P < 5ms)	-2	А
Ptot	Total dissipation at T _{amb} = 25°C	0.5	W
Tstg	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3: Thermal data

Symbol	Parameter	Value	Unit
Rthj-amb ⁽¹⁾	Thermal resistance junction-amb max	250	°C/W

Notes:

⁽¹⁾Device mounted on PCB area of 1 cm²



2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

	Table 4:	Electrical	characteristics
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Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Ісво	Collector cut-off current (I _E =0)	V _{CB} = -60 V			-0.1	μA
Іево	Emitter cut-off current (I _C =0)	V _{EB} = -5 V			-0.1	μA
V(br)cbo	Collector-base breakdown voltage (I _E = 0)	Ic = -100 μA	-60			V
V(br)ceo ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = -10 mA	-60			V
V _{(BR)EBO}	Emitter-base breakdown voltage (Ic = 0)	I _E = -100 μA	-5			V
V _{CE(sat)}	Collector-emitter	$I_{C} = -0.5 \text{ A} I_{B} = -50 \text{ mA}$			260	mV
VCE(sat)	saturation voltage	$I_{C} = -1 \text{ A } I_{B} = -100 \text{ mA}$			480	mV
V _{BE(sat)}	Base-emitter saturation voltage	Ic = -1 A I _B = -100 mA			1.3	V
		$I_{C} = -0.5 \text{ A V}_{CE} = -2 \text{V}$	180		560	
h _{FE}	DC current gain	$I_{C} = -1 \text{ A } V_{CE} = -2 \text{ V}$	45			
		$I_{C} = -2 A V_{CE} = -2 V$		30		
	Resistive load					
t _{on}	Turn-on time	$I_{C} = -1.5 \text{ A V}_{CC} = -10 \text{ V}$		220		ns
t _{off}	Turn-off time	$I_{B1} = -I_{B2} = -150 \text{ mA}$ $V_{BB(off)} = 5 \text{ V}$		500		ns

Notes:

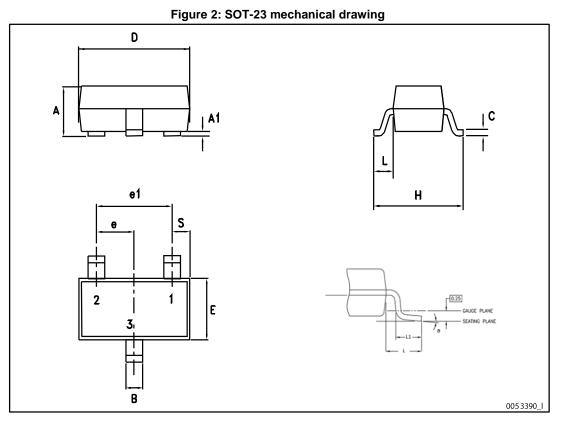
 $^{(1)}\text{Pulse test:}$ pulse duration = 300 µs, duty cycle \leq 1.5 %



3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

3.1 SOT-23 mechanical data

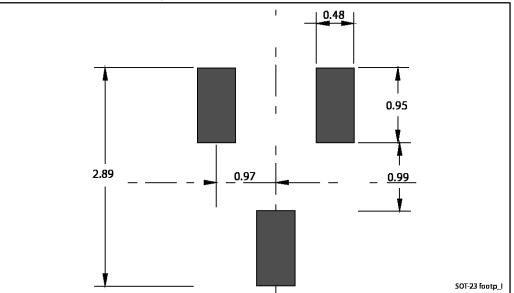




Package mechanical data

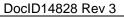
Table 5: SOT-23 mechanical data					
D	mm				
Dim.	Min.	Тур.	Max.		
A	0.89		1.40		
A1	0		0.10		
В	0.30		0.51		
С	0.085		0.18		
D	2.75		3.04		
е	0.85		1.05		
e1	1.70		2.10		
E	1.20		1.75		
Н	2.10		3.00		
L		0.60			
S	0.35		0.65		
L1	0.25		0.55		
а	0°		8°		







Dimensions are in mm.





4 Revision history

Table 6: Document revision history

Date	Revision	Changes
18-Jun-2008	1	Initial release
08-May-2014	2	Updated Section 3: "Package mechanical data".
13-Mar-2015	3	Updated marking in Table 1: "Device summary"



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